Optical injection of spin current in zigzag nanoribbon of monolayer $MoS_2$ with antiferromagnetic Kekule distortion

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Kekule pattern of (anti)ferromagnetic exchange field on the monolayer $MoS_2$ could be induced by proximity to the (111) surface of $BiFeO_3$ on both sides. The magnetization orientations of the substrates control the pattern of exchange field, which in turn switch the band structures of the lowest zigzag edge states between being metallic and insulating. The lowest four zigzag edge bands provides conducting channels with spin-polarized current. Optical excitation of carriers in these bands generate sizable spin and charge currents, which is theoretically modelled by the perturbation solution of the semiconductor Bloch equation.

I. INTRODUCTION

Transition metal dichalcogenides (TMDs) are exotic two-dimensional materials with large spin-orbit coupling (SOC), which in turn exhibit spintronic and valleytronic physics [1, 2]. Optical excitation of valley polarized exciton [3] have been realized in experiment [4–9] and proposed as valleytronic devices [10, 11]. On the other hand, optical injection of spin current in monolayer TMDs have been studied and proposed as spintronic devices [12, 13]. Because the band gaps of the TMDs vary between 1 eV and 1.5 eV [14, 15], the optical frequency is limited within the range of near-infrared and visible light. Proximity to ferromagnetic substrate induces spatially uniform ferromagnetic exchange field on the TMDs layer, which in turn induces valley splitting [16]. Because the inversion symmetric is broken, Rashba SOC is induced. As a result, the spin mixing and canted spins are generated in the bulk and zigzag edge states. Recently theoretical study suggested that the zigzag edge states with canted spin carry sizable spin current with appropriate Fermi level [16]. Optical excitation of carrier at the zigzag edge states requires smaller optical frequency, which could be around 0.1 eV. As a result, these systems open a door for opto-spintronic with far-infrared optical field as excitation source. The systems host spatially localized spin current as information carrier. On the other hand, recent develop of antiferromagnetic spintronic propose replacement of ferromagnetic by antiferromagnetic materials in spintronic devices, because antiferromagnetic materials are superior in several aspect, such as the absence of parasitic stray fields and ultrafast magnetization dynamics [17–20]. As a result, we consider replacing the ferromagnetic substrate of the TMDs zigzag nanoribbon by antiferromagnetic substrate. If the substrate is (111) surface of $MnO$, the $Mn$ atoms at the surface is lattice match with the $Mo$ or $W$ atoms with uniform exchange field [21], so that the model is the same as the system with ferromagnetic substrate. However, if the substrate is (111) surface of $BiFeO_3$, the exchange field has Kekule pattern as explained in the following.

Graphene is a typical two-dimensional material, whose band structure have two Dirac cones designated as $K$ and $K'$ valleys [22]. Optical injection of spin current to graphene has been proposed as candidate of opto-spintronic devices [23–28]. The schemes for excitation of localized spin currents along zigzag edges or domain walls make integrated opto-spintronic devices feasible [27]. Proximity to substrate with the same lattice structure but lattice constant being $\sqrt{3}$ times larger than that of graphene induces Kekule distortion [29–32]. One example is graphene on $In_2Te_3$ [32]. A $\sqrt{3} \times \sqrt{3}$ supercell of graphene is conformal with the primitive unit cell of the substrate. The band folding in the supercell bring the $K$ and $K'$ valleys to the $\Gamma$ point in the Brillouin zone. The Kekule distortion mix the quantum states of the two valleys, which open a bulk gap.

We consider the Kekule distortion of monolayer $MoS_2$, which is induced by intercalating the $MoS_2$ between two substrates with (111) surface of $BiFeO_3$, et.al. the $BiFeO_3/MoS_2/BiFeO_3$ heterostructure. Experimental fabrication of the monolayer $MoS_2/BiFeO_3$ heterostructure is feasible [34]. At room temperature, $BiFeO_3$ is G type antiferromagnetic, so that all $Fe$ atom at the same (111) plane have the same magnetization orientation [35]. The $Fe$ atom on the (111) surface arrange in triangular lattice with lattice constant being 5.5195 Å, which is only 0.1% mismatch with $\sqrt{3}$ times of the lattice constant of $MoS_2$, which is $a_0 = 3.19$ Å. The $Y$ type Kekule distortion is assumed in this study, et.al. the $Fe$ atom is on top of one of the three $Mo$ atoms in a unit cell. The magnetization of the $Fe$ atom induce larger and smaller exchange field at the nearest $Mo$ atom and the other two $Mo$ atoms, respectively. Both side of the $MoS_2$ have substrates. We assume that the $Fe$ atoms at different sides are on top of different $Mo$ atoms. By rotating the

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magnetization orientation of the two substrates, the exchange fields of the three Mo atoms could be changed, which in turn control the band structure of the zigzag edge states. With appropriate Kekule pattern of the exchange field and energy level, the forward and backward moving zigzag edge modes have opposite spins. Optical excitation of carriers to these modes generate sizable spin current, which is localized at the Mo terminated zigzag edge.

The article is organized as following: In section II, the atomic structure of the BiFeO$_3$/MoS$_2$/BiFeO$_3$ heterostructure is described, and the effective tight binding Hamiltonian is described. In section III, the band structures and spin texture of zigzag nanoribbons are discussed. In section IV, the optical injection of spin current and the local magnetic moment. The spin Hall effect at the lattice sites plotted as circle dots are a result, the exchange field at the lattice sites plotted as different shapes of triangles (downward-pointing triangles) lattice sites, and depends on the interlayer distance between the layers. The parameter $\lambda$ is nearly one; for the other extreme case with large interlayer distance, which is assumed to be $M_{B} + |M_{T}|$, the exchange field at the other Mo atoms that are not on top of the Fe atom. We assume that the Fe atoms of the bottom (top) BiFeO$_3$ substrates are on top of the Mo atomic lattice sites that are plotted as upward-pointing triangles (downward-pointing triangles) in Fig. 1(a). Thus, the bottom (top) BiFeO$_3$ substrates induce exchange field $M_{\uparrow}$ ($M_{\downarrow}$) at the upward-pointing triangles (downward-pointing triangles) lattice sites, and $\lambda M_{B} + \lambda M_{T}$ at the other lattices. The parameter $\lambda > 1$ depends on the interlayer distance between MoS$_2$ and BiFeO$_3$. For the extreme case with large interlayer distance, $\lambda$ is nearly one; for the other extreme case with small interlayer distance, $\lambda$ is nearly zero. We assume the parameter being $\lambda = 0.25$. The strength of the exchange field $B_{0} = |M_{B}| + |M_{T}|$ is also dependent on the interlayer distance, which is assumed to be $B_{0} = 125$ meV. As a result, the exchange field at the lattice sites plotted as upward-pointing triangles, downward-pointing triangles and circle dots are $M_{\uparrow} = M_{B} + \lambda M_{T}$, $M_{\downarrow} = \lambda M_{B} + M_{T}$ and $M_{\circ} = \lambda M_{B} + \lambda M_{T}$, respectively.

The heterostructure is modelled by the Hamiltonian $H = H_{MoS_2} + H_{ex} + H_{R}$. The Hamiltonian of the monolayer MoS$_2$ is given by the three bands tight binding model with three d orbital basis $\{|d_{z^2}, s\}, |d_{xy}, s\}, |d_{z^2-y^2}, s\}$ and spin index $s = \pm 1$. The interaction $\{d_{xy}, s\}$-orbital mixing matrix for each lattice site. The detail form of the Hamiltonian $H_{MoS_2}$ and $H_{R}$ can be found in reference [14]. The Hamiltonian of the exchange field is given as $H_{ex} = \sum_{\sigma} M_{cvv} \otimes (M_{1} \cdot \sigma)$, with the summation cover all lattice site. $M_{cvv} = diag\{1, 0.8252, 0.8252\}$, $\sigma = \hat{x} \sigma_{x} + \hat{y} \sigma_{y} + \hat{z} \sigma_{z}$ and $\sigma_{x,y,z}$ being the Pauli matrix. The diagonal matrix element of $M_{cvv}$ is the magnetic coupling coefficient to the conduction and valence bands.

III. THE BAND STRUCTURE

The band structure of the zigzag nanoribbon with $N_{zig} = 5$ unit cell along the transversal direction can be obtained by diagonalization of the Hamiltonian with Bloch periodic boundary along the zigzag direction. In addition to the bulk states, edge states with energy within the bulk gap are found. For pristine MoS$_2$ zigzag nanoribbon, the unit cell is three times smaller than that in Fig. 1(a) along the zigzag direction; the band structures of the edge states are connected to the conduction bands and have finite gap from the valence bands [14]. By choosing the unit cell in Fig. 1(a), the two band valleys at the $K$ and $K'$ points are folded into the $\Gamma$ point, i.e. $k_{x} = 0$. In the presence of Kekule pattern of the magnetic exchange field, the two band valleys are coupled, which modifies the band structure of bulk and edge states. The

![Image](image.png)
band structure of the edge state are shown in Fig. 2. If the magnetization orientation of the bottom substrate is fixed, the rotation of the magnetization orientation of the top substrate between being parallel or anti-parallel to that of the bottom substrate change the band structures. For the edge state that are located on the Mo-edge termination, the lowest band is switched between being isolated from or being connected to the second lowest band. Similarly, the second lowest band is switching between being isolated from or being connected to the third lowest band. For the neutral system, the Fermi level fills up to the lowest six edge bands. With hole doping of \(5/(36N_{z1g})\) or \(4/(36N_{z1g})\) in the MoS\(_2\), the Fermi level fills up to the lowest or second lowest band, respectively. Thus, the nanoribbon is switched between insulating and metallic by the rotation of the magnetization orientation, which could function as spin valve [30, 37]. For the four bands of the edge states located on the \(S\)-edge termination, the gap between the lower two bands and the higher two bands is also switched on and off by the rotation of the magnetization orientation. However, if the Fermi level is within this gap, the edge states located on the \(Mo\)-edge termination are always conducting, so that the system could not function as spin valve.

Because of the Kekule pattern of the exchange field, the edge state could support one-way spin current. We focus on the system with magnetization orientation of substrates being \(\mathbf{M}_B = -\mathbf{M}_T = B_0 \hat{z}\) (the system in Fig. 2(c)). The charge and spin current is characterized by the velocity and spin-velocity operator, which are defined as \(\hat{v}_x = (1/\hbar) \partial H/\partial k_x\) and \(\hat{s}_{x,\kappa} = \frac{1}{2} (\hat{v}_x \sigma_\kappa + \sigma_\kappa \hat{v}_x)\), respectively, where \(k_x\) is the wave vector along the zigzag nanoribbon and \(\kappa = x, y, z\). The band structure that exhibit the expectation value of the velocity and spin-velocity operators as color scale are plotted in Fig. 3. The band structure is symmetric under \(k_x \leftrightarrow -k_x\). The velocity of the edge states is proportional to the slope of the band structures. Within the energy ranges marked by the grey area in Fig. 3(b-d), there are only two edge states with opposite velocities at each energy level. The spin-\(x\) (spin-\(y\), spin-\(z\)) component of the two edge states is the same with (opposite to) each other, so that the expectation of the spin-velocity operator is opposite to (the same with) each other. For the spin-\(y\) and spin-\(z\) components, this property could be designated as one-way spin-velocity texture. In the absence of the Kekule pattern of the exchange field, these energy ranges vanish. Optical excitation of carriers within these energy ranges could injects large spin current with \(y\) and \(z\) components, because the forward and backward traveling electrons carry spin current with the same sign. As comparison, the spin current with \(x\) component would be smaller, because the forward and backward traveling electrons carry spin current with opposite sign. Because the inversion symmetric

![Figure 2](image2.png) FIG. 2: The band structure of the zigzag nanoribbon with width being \(5\sqrt{3}a_0\). The edge states that are located on the \(Mo\)- and \(S\)-edge terminations are plotted as solid (blue) and dashed (red) lines, respectively. The orientation of the magnetization in the substrates are: \(\mathbf{M}_B = B_0 \hat{z}\) in (a), \(\mathbf{M}_T = B_0 \hat{z}\) in (a), \(\mathbf{M}_T = B_0 \hat{x}\) in (b), \(\mathbf{M}_T = -B_0 \hat{z}\) in (c); \(\mathbf{M}_B = B_0 \hat{x}\) in (d-f), \(\mathbf{M}_T = B_0 \hat{x}\) in (d), \(\mathbf{M}_T = B_0 \hat{y}\) in (e), \(\mathbf{M}_T = -B_0 \hat{x}\) in (f); \(\mathbf{M}_B = B_0 \hat{y}\) in (g-i), \(\mathbf{M}_T = B_0 \hat{y}\) in (g), \(\mathbf{M}_T = -B_0 \hat{x}\) in (h), \(\mathbf{M}_T = -B_0 \hat{y}\) in (i).

![Figure 3](image3.png) FIG. 3: The band structure of the zigzag nanoribbon with width being \(5\sqrt{3}a_0\), and magnetization orientation of substrates being \(\mathbf{M}_B = -\mathbf{M}_T = B_0 \hat{z}\) (the same as that in Fig. 2(c)). In (a), the bulk states are plotted as thin black lines; the edge states of the \(Mo\)- and \(S\)-edge terminations are plotted as thin and thick lines with color. The color scale exhibits the expectation value of the velocity operator in the unit of \(nm/\text{fs}\). In figures (b), (c) and (d), the energy range is zoomed in; the color scale exhibits the expectation value of the spin-velocity operator in the unit of \(nm/\text{fs}\), for the spin component along \(\hat{x}\), \(\hat{y}\) and \(\hat{z}\), respectively.
is absent, the non-diagonal matrix elements of the velocity operator are not symmetric under $k_x \leftrightarrow -k_x$. Thus, optical excitation generates different populations of carriers at the forward and backward traveling edge states, which in turn injects charge current.

IV. OPTICAL SPIN INJECTION

The optical excitation is modelled by the semiconductor Bloch equation \cite{27, 28}. In the presence of optical field, the Hamiltonian has additional interaction term given as

$$H_I = -\frac{e_0}{m_0 c} \mathbf{A}(t) \cdot \mathbf{P}$$  \hspace{0.5cm} (1)

where $e_0$ is electron charge, $m_0$ is electron mass, $c$ is speed of light and $\mathbf{A}$ is the vector potential. Under the Coulomb gauge, the electric field is given as $\mathbf{E} = -\frac{1}{c} \frac{\partial \mathbf{A}(t)}{\partial t}$. We consider single frequency harmonic optical field with linear polarization along $\hat{x}$ direction and frequency being $\omega$, so that $\mathbf{E} = Re\{E_0 e^{-i \omega t}\} \hat{x}$. In realistic experimental condition, the plane wave of the optical field is approximated by center part of the Gaussian beam with beam width being one wavelength in vacuum, so that the relation between the power of the Gaussian beam and the amplitude of the optical field is approximated as $E_0 = \pi \omega Z_0 \kappa_0$, with $Z_0 = 376.73 \Omega$ being the impedance of free space. We assumed $P_0 = 10^{-5}$ W, so that $E_0$ is a function of the optical frequency in our numerical simulation. The momentum operator along $\hat{x}$ direction is given by the velocity operator as $P_x = m_0 \partial H/\partial k_x$. Thus, the interaction Hamiltonian is given as

$$H_I = i\frac{e_0 E_0}{\hbar \omega} \frac{\partial H}{\partial k_x} e^{-i \omega t} - i\frac{e_0 E_0}{\hbar \omega} \frac{\partial H}{\partial k_x} e^{i \omega t}$$  \hspace{0.5cm} (2)

The time evolution of the density matrix obeys the semiconductor Bloch equation with relaxation time approximation, given as

$$ih \frac{\partial \rho(t)}{\partial t} = [\rho(t), H + H_I] - \frac{\hbar}{\tau} [\rho(t) - \rho(0)(t)]$$  \hspace{0.5cm} (3)

where $\tau$ is the relaxation time of the edge states. We assume $\tau = 1$ ps. The perturbation solution could be expanded as $\rho(t) = \rho^{(0)} + \rho^{(1)}(t) + \rho^{(2)}(t) + \cdots$, with $\rho^{(0)}$ being diagonal matrix whose matrix element is given by the Dirac-Fermi distribution at temperature $T$. We assume room temperature with $k_B T = 0.025852$ eV in the numerical studies. The second order perturbation solution $\rho^{(2)}(t)$ includes second harmonic terms with time dependent factor $e^{\pm 2i \omega t}$ and zero harmonic terms $\rho^{(2)}_0$ that is independent of time. The injection of the direct charge and spin current is obtained by the expectation of the velocity and spin-velocity operator by the zero harmonic terms of $\rho^{(2)}(t)$, given as

$$I_e = -\frac{e_0}{3 N_k a_0} \sum_{k,n,n'} \langle k, n | \hat{v}_x | k, n' \rangle \rho^{(2)}_0$$  \hspace{0.5cm} (4)

$$P_s^x = \frac{e_0}{3 N_k a_0} \sum_{k,n,n'} \langle k, n | \hat{s}_{x, \kappa} | k, n' \rangle \rho^{(2)}_0$$  \hspace{0.5cm} (5)

where $N_k$ is the number of sampling point of the Bloch wave number $k$.

The optical injection of charge and spin currents in the system with magnetization orientation of substrates being $M_B = -M_T = B_0 \hat{z}$ (the same as the system in Fig. 2(c) and Fig. 3) versus frequency of the optical field are plotted in Fig. 4(a) and (b), with Fermi energy level being $E_{F1}$ and $E_{F2}$, respectively. The charge current is small but nonzero, because the excited population of edge states at $k_x$ and $-k_x$ at the same energy level is different. In most range of optical frequency, $I_{s}^{x,z}$ is larger than $I_{s}^{x}$, which confirm the inference in the previous section. The spin currents peak at several resonant frequencies, which is the result of the competition between the spin current generated by the edge states within and outside of the energy ranges with one-way spin-velocity texture (those in the grey area in Fig. 3(b-d)). For example, for the first resonant peak at optical frequency $\hbar \omega = 0.028$ eV, the optically excited carriers populated around the band crossing around the energy level $E_{F2}$. As the optical frequency decrease, no carrier populated within the energy ranges in the grey area, so that the magnitude of the spin currents sharply decrease. As the optical frequency increase, more carrier populated outside the energy ranges in the grey area, which cancel the total spin currents, so that the magnitude of the spin current smoothly decrease. For the case in Fig. 3(b), although the Fermi level $E_{F1}$ is away from the band crossing around energy level $E_{F2}$, equilibrium population (i.e. diagonal terms of $\rho^{(0)}$)}
at room temperature around the band crossing is sizable. Thus, the optical field can excite electron and hole at the upper and lower part of the band crossing, respectively. Therefore, the resonant peak exist. If the Fermi level is raised to $E_F$ as in the case in Fig. 4(b), the equilibrium population contrast between the upper and lower part of the band crossing is larger, so that the amplitude of the resonant peak becomes larger. As comparison, for suspended $MoS_2$ nanoribbon that have not exchange field, the spin currents have not any resonant peak versus optical frequency, and the maximum spin current is smaller than 0.1 pA.

If the magnetization orientation of substrates are switched to be parallel, i.e. $M_B = M_T = B_0 \hat{z}$, the optical injection of charge and spin currents are plotted in Fig. 4(c) and (d). In this cases, the first few resonant peaks are switched off. The spin currents at the corresponding optical frequency is smaller than 0.1 pA. A few resonant peaks at larger optical frequency with smaller magnitude appear. This property could function as optical spin valve, because the spin currents are switched on and off by the rotation of the magnetization orientation.

V. CONCLUSION

In conclusion, intercalation of monolayer $MoS_2$ between two $BiFeO_3$ substrates could induce Kekule pattern of exchange field in the $MoS_2$ layer, which is controlled by the magnetization orientation of the substrates. By employing tight binding model, the numerical simulation reveal that the band structures and spin texture of the zigzag nanoribbon are dependent on the pattern of the exchange field. The edge bands could be switched between metallic and insulating. With anti-parallel magnetization orientation of the substrates, large energy ranges with one-way spin-velocity texture for spin-y and spin-z components are found. The property enhance the optical injection of spin current. When the optical excitation generate maximum population of edge state with one-way spin-velocity, the injected spin current peaks. If the magnetization orientation of the substrates are switched to be parallel, the peaks are turn off because the band structures and spin texture are changed. As a result, the optical excitation of localized spin current at the zigzag edge is controlled by the magnetization orientation of the substrates.

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References


